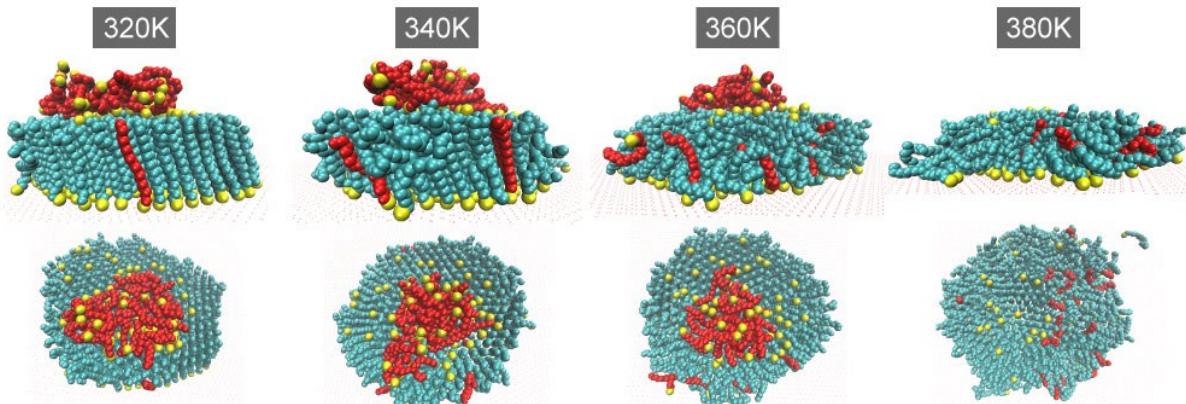


## Supporting Information

# Thermal Curing of Self-Assembled Monolayer at the Nanoscale

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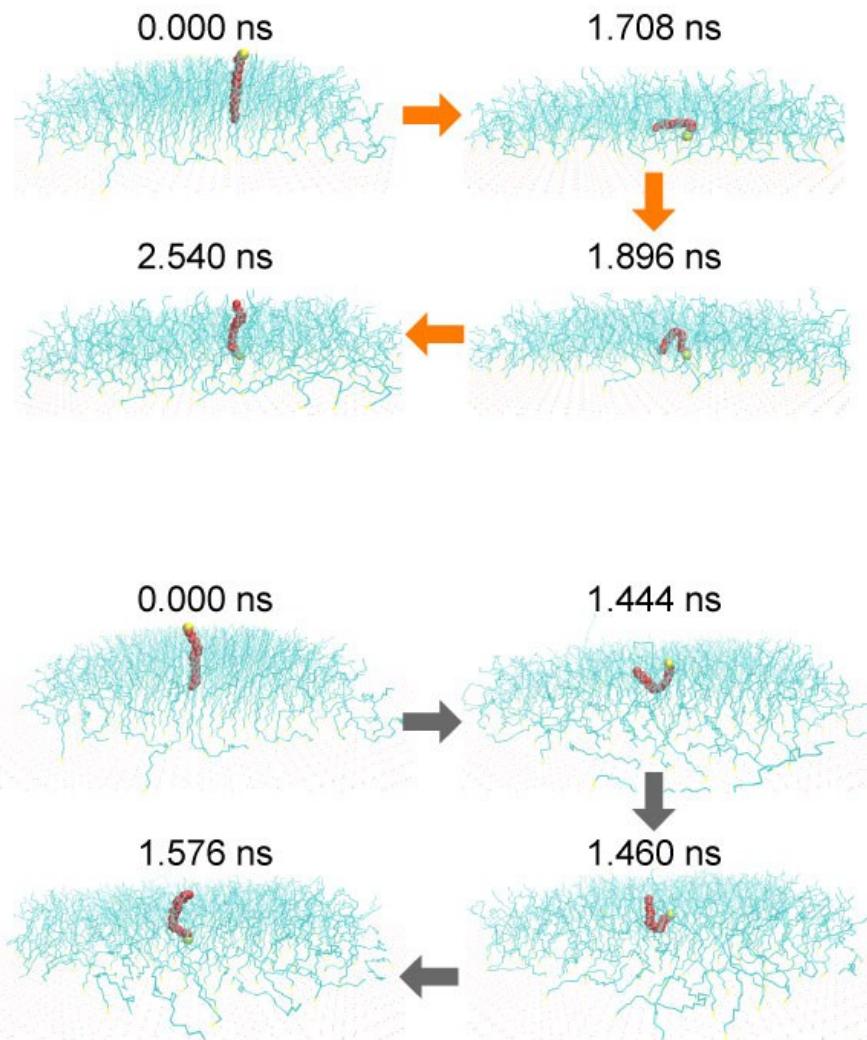


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2 **Fig. S1** Adsorption of molecules piled on top of the SAM island in the thermal annealing.  
 3 Representative MD snapshots at 320, 340, 360, and 380 K are shown. The side and top views at  
 4 each temperature are shown in the top and bottom rows, respectively. The unbound molecules  
 5 piled on top of the SAM island at 300 K appear in red. At 320 K, only one molecule was found  
 6 hopping down to the surface. At 340 K, four more molecules hopped down and only one  
 7 adsorbed via the push-down pathway. At 360 K, four more molecules hopped down. At 380 K,  
 8 five molecules adsorbed by following the hop-down path. The remaining 17 molecules followed  
 9 the push-down pathway to achieve adsorption.

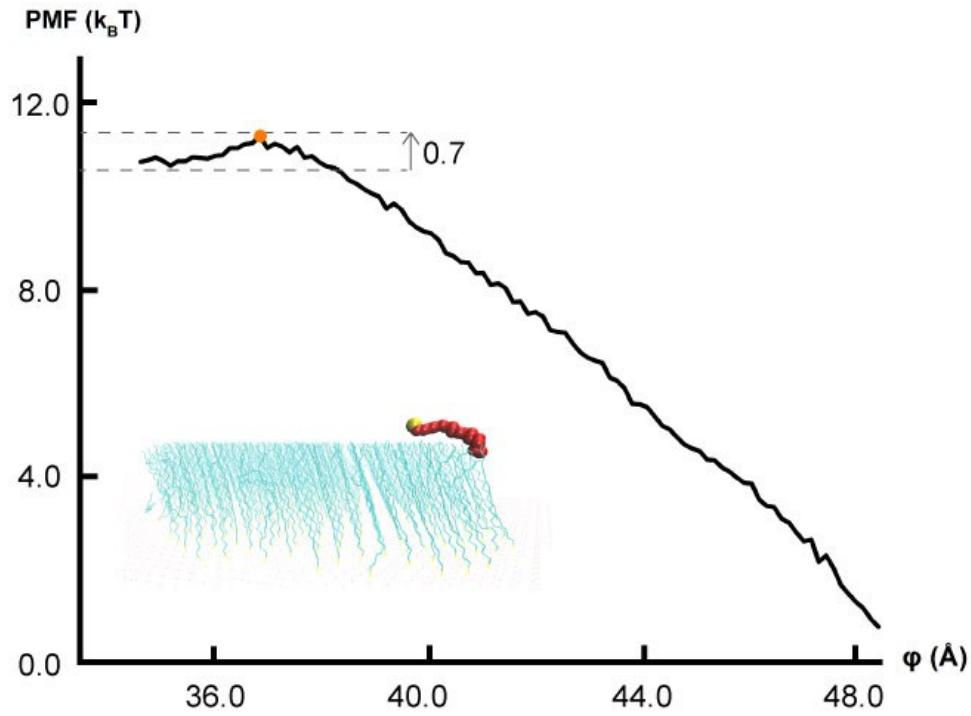
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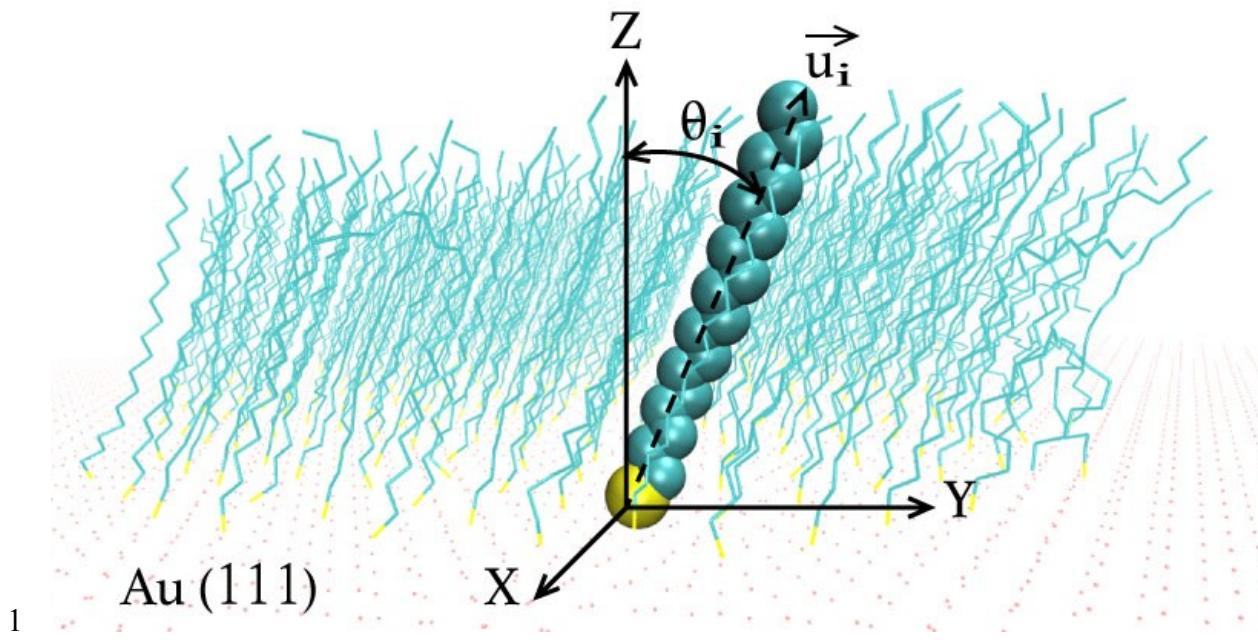
2 **Fig. S2** Flipping of an inverted molecule at 400 K. An inverted molecule flipped by moving its  
 3 sulfur atom down and methyl tail group up either sequentially (top) or simultaneously (bottom).  
 4 In the sequential flip pathway (top), the sulfur atom of an inverted molecule penetrates down  
 5 without moving its methyl tail group. After the sulfur atom adsorbs, the methyl tail group moves  
 6 up to yield an upright molecule. In the simultaneous flip pathway (bottom), the sulfur atom of an  
 7 inverted molecule lowers while raising its methyl tail group at the same time.



1

2 **Fig. S3** Potential of mean force (PMF) profile for the adsorption of an ODT molecule via the  
 3 hop-down pathway. Unlike the PMF profile shown in Fig. 4, the free energy profile above is  
 4 obtained by removing the pile of molecules on top of the SAM island except the adsorbing  
 5 molecule (in red). The free energy barrier,  $0.7 k_B T$  in height, is an analog of the Ehrlich-  
 6 Schwoebel barrier in the epitaxial growth of a metallic film. Also depicted is the configuration of  
 7 the transition state.

8



1 **Fig. S4** Orientation of an ODT molecule adsorbed on the gold (111) surface. Highlighted is the  
 2 *i*th molecule (out of 346 molecules) with all trans conformations. The tilt direction vector,  $\vec{u}_i$ ,  
 3 was defined by selecting  $\text{CH}_3$  or  $\text{CH}_2$  groups with odd (1–17) numbers of intervening  $\text{CH}_2$   
 4 groups between them and the sulfur atom. The unit vector,  $\vec{u}_i$ , was defined as the average of the  
 5 vectors from the sulfur atom to these selected groups. The tilt angle  $\theta_i$  is the polar angle of  $\vec{u}_i$   
 6 measured from the surface normal (Z direction).  
 7

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1 **Table S1** Structural parameters of the present SAM island after completion of thermal annealing.  
 2 Listed are the average values of the sulfur-sulfur distance,  $d_{ss}$ , tilt angle of alkyl chains,  $\theta$ ,  
 3 percentage of trans conformations, % trans, and orientational order parameter of alkyl chains,  $O_u$ .  
 4 The corresponding values from the MD simulation of the bulk SAM without defects are listed  
 5 for comparison. Also listed, in the third and fourth rows, are the results for the SAM islands  
 6 annealed two and four times faster than in the present simulation, respectively. Decreasing the  
 7 annealing rate enhances the quality of the SAM island, as manifested in the values of % trans and  
 8  $O_u$ .

	$d_{ss}$	$\theta$	% trans	$O_u$
Present SAM island	4.97 Å	26.1°	97.1%	0.92
Bulk SAM without defects	4.99 Å	29.0°	99.0%	0.98
SAM island annealed 2x faster	5.00 Å	26.4°	96.3%	0.88
SAM island annealed 4x faster	4.99 Å	26.0°	95.1%	0.78

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